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INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶ : C11D 3/30, 3/43, G03C 11/12, H01L 21/304, 21/3065		A1	(11) International Publication Number: WO 99/19447 (43) International Publication Date: 22 April 1999 (22.04.99)
(21) International Application Number: PCT/US98/21807 (22) International Filing Date: 14 October 1998 (14.10.98)		(81) Designated States: CA, ID, IL, JP, KR, SG, US, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).	
(30) Priority Data: 60/062,856 14 October 1997 (14.10.97) US		Published <i>With international search report.</i>	
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(54) Title: AMMONIUM BORATE CONTAINING COMPOSITIONS FOR STRIPPING RESIDUES FROM SEMICONDUCTOR SUBSTRATES

(57) Abstract

The present invention comprises formulations for stripping wafer residues which originate from a halogen based plasma metal etching followed by oxygen plasma ashing. The formulations contain the following general components (percentages are by weight): an organic amine or mixture of amines 15–60 %, water 20–60 %, ammonium tetraborate or ammonium pentaborate 9–20 %, an optional polar organic solvent 0–15 %.

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